

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8178	(microloading near effect) or over-etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:05
L2	200999	(contact near hole\$1) or (contact near plug\$1) or through-hole\$1 or viahole\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:06
L3	44030	etch\$3 near2 rat\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:06
L4	1450	I1 and I2 and I3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:07
L5	582854	(insulat\$3 near (layer or film)) or (dielectric near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:08
L6	1360	I4 and I5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:09
L7	240149	FET or MOSFET or (field near effect near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 12:10
L8	342	I6 and I7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 13:35
L9	9278	(438/634 or 438/637 or 438/649 or 438/655 or 438/656 or 438/667 or 438/668 or 438/672 or 438/675 or 438/709 or 438/710 or 438/712).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 13:42

L10	3015	I9 and I2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 13:42
L11	861	I10 and I3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 13:43
L12	808	I11 and I5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/20 13:43